



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SD103AWT-SD103CWT

## SOD-523 Schottky Barrier Diode 肖特基势垒二极管

### Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	SD103AWT	SD103BWT	SD103CWT
Pin 管脚			
Mark 打标	S4	S5	S6

### Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Reverse Voltage/ Repetitive Reverse Voltage 反向电压/重复反向电压	SD103AWT SD103BWT SD103CWT	$V_R/V_{RRM}$	40 30 20 V
Forward Work Current 正向工作电流	$I_o$	350	mA
Peak Forward Surge Current 正向峰值浪涌电流	$I_{FSM}$	2000	mA
Power dissipation 耗散功率	$P_D(T_a=25^\circ C)$	150	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	668	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-65to+125 $^\circ C$	

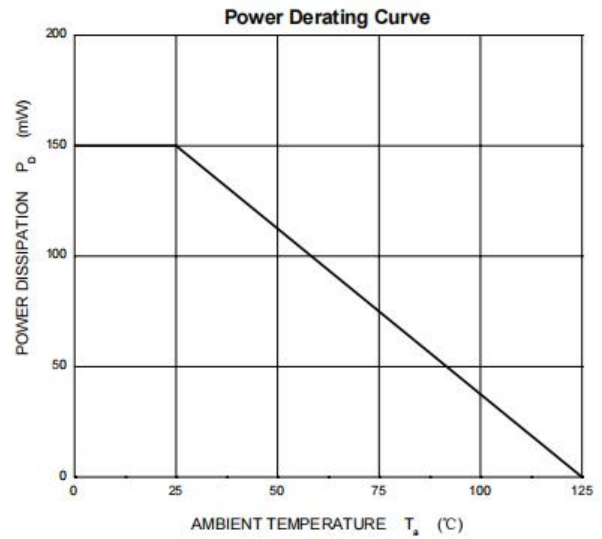
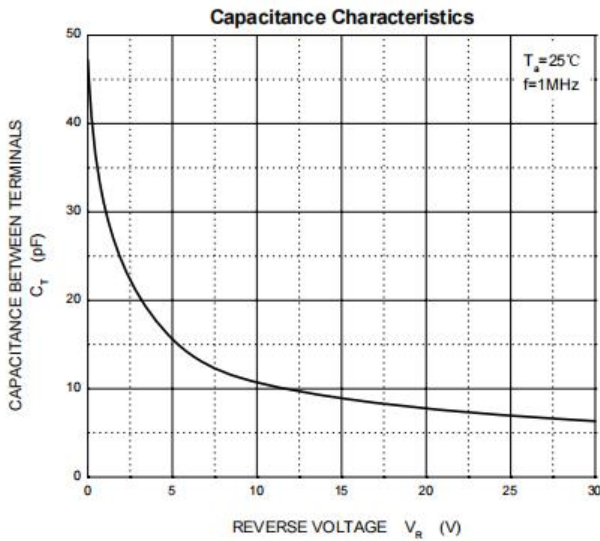
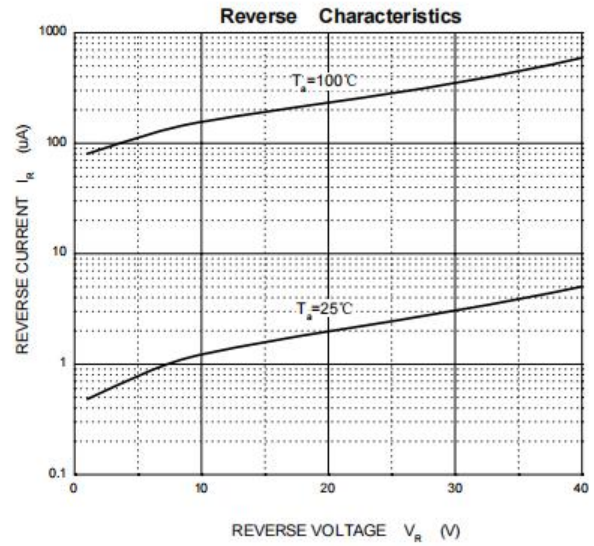
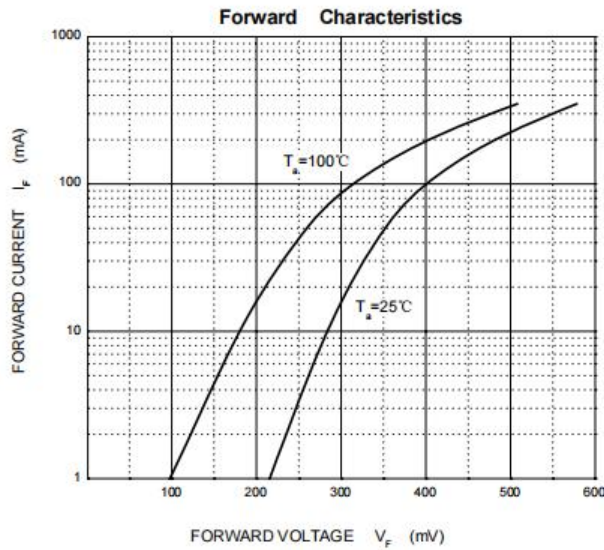
### Electrical Characteristics 电特性

( $T_A=25^\circ C$  unless otherwise noted 如无特殊说明, 温度为 25 $^\circ C$ )

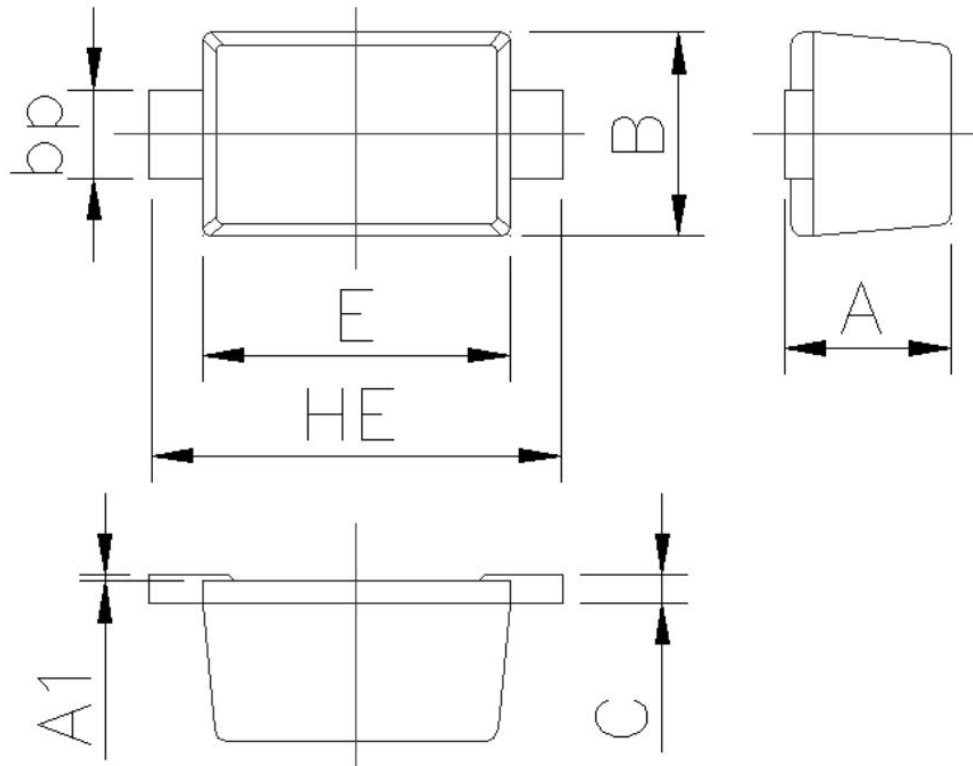
Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压 ( $I_R=10\mu A$ )	SD103AWT SD103BWT SD103CWT	$V_{(BR)}$	40 30 20	V
Reverse Leakage Current( $V_R=30V$ ) 反向漏电流( $V_R=20V$ ) ( $V_R=10V$ )	SD103AWT SD103BWT SD103CWT	$I_R$	5 — 5	$\mu A$
Forward Voltage( $I_F=20mA$ ) 正向电压( $I_F=200mA$ )	$V_F$	—	0.37 0.6	V
Diode Capacitance 二极管电容( $V_R=0V, f=1MHz$ )	$C_D$	—	50	pF
Reverse Recovery Time 反向恢复时间	$T_{rr}$	—	10	nS



## ■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70